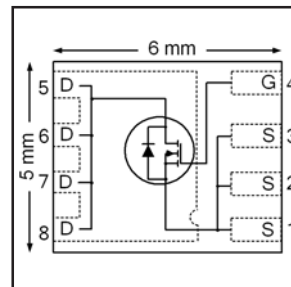


HEXFET® Power MOSFET

$V_{DS}$	<b>75</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = 10V$ )	<b>5.9</b>	<b>mΩ</b>
$Q_g$ (typical)	<b>65</b>	<b>nC</b>
$R_G$ (typical)	<b>1.2</b>	<b>Ω</b>
$I_D$ (@ $T_{mb} = 25^\circ C$ )	<b>100</b> Ⓢ	<b>A</b>



### Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

### Features and Benefits

#### Features

Low $R_{DS(on)}$ ( $\leq 5.9m\Omega$ )
Low Thermal Resistance to PCB ( $\leq 0.8^\circ C/W$ )
100% Rg tested
Low Profile ( $\leq 0.9$ mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

#### Benefits

Lower Conduction Losses
Enables Better Thermal Dissipation
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

results in  
⇒

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH5007PBF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH5007TRPBF

### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	75	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	17	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	13	
$I_D @ T_{mb} = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	100Ⓢ	
$I_D @ T_{mb} = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	88	
$I_{DM}$	Pulsed Drain Current ①	400	
$P_D @ T_A = 25^\circ C$	Power Dissipation ⑤	3.6	W
$P_D @ T_{mb} = 25^\circ C$	Power Dissipation ⑤	156	
	Linear Derating Factor ⑤	0.029	W/°C
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		

Notes ① through ⑤ are on page 8

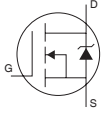
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	75	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.09	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	5.1	5.9	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 150μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-8.4	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	100	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 50A
Q <sub>g</sub>	Total Gate Charge	—	65	98	nC	V <sub>DS</sub> = 38V V <sub>GS</sub> = 10V I <sub>D</sub> = 50A See Fig. 17 & 18
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	11	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	4.5	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	20	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	29.5	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	24.5	—		
Q <sub>oss</sub>	Output Charge	—	21	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	1.2	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	10	—	ns	V <sub>DD</sub> = 38V, V <sub>GS</sub> = 10V I <sub>D</sub> = 50A R <sub>G</sub> = 1.8Ω See Fig. 15
t <sub>r</sub>	Rise Time	—	14	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	30	—		
t <sub>f</sub>	Fall Time	—	11	—		
C <sub>iss</sub>	Input Capacitance	—	4290	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	510	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	210	—		

**Avalanche Characteristics**

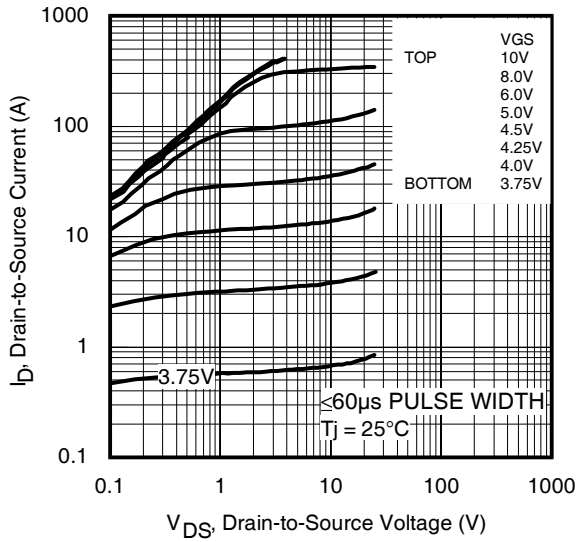
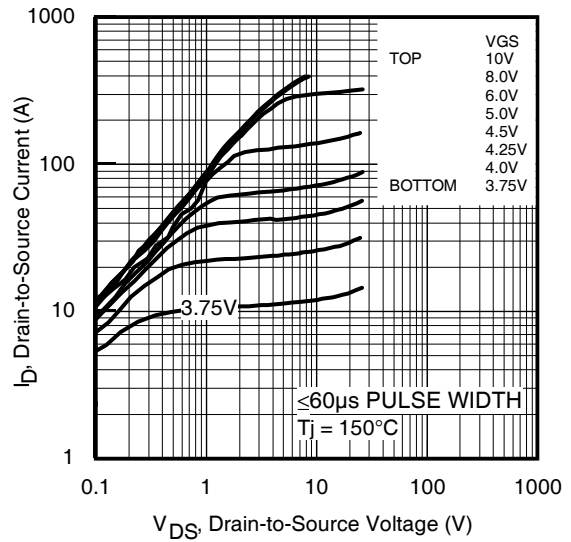
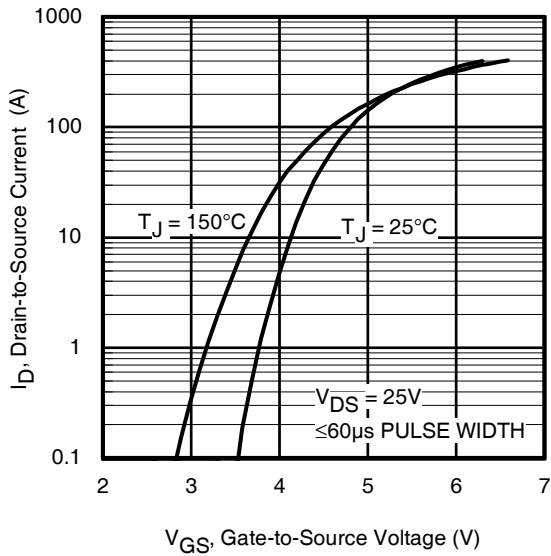
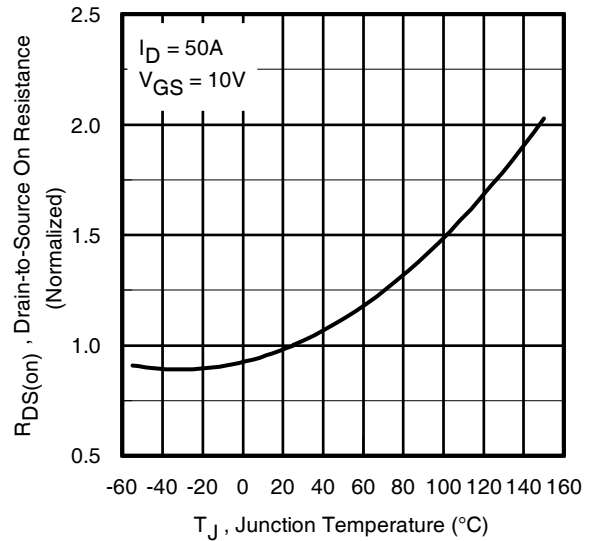
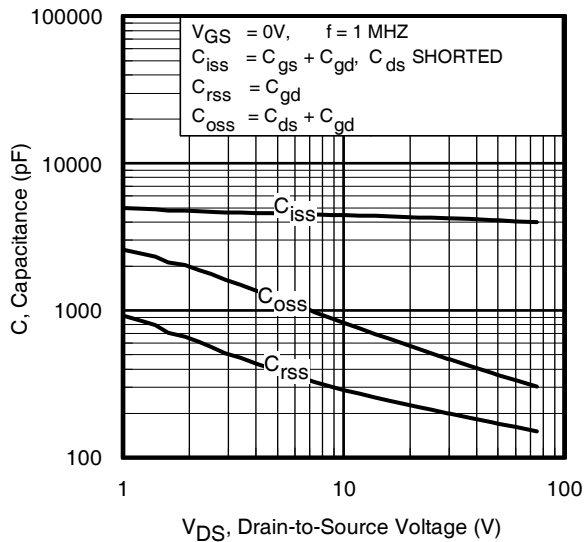
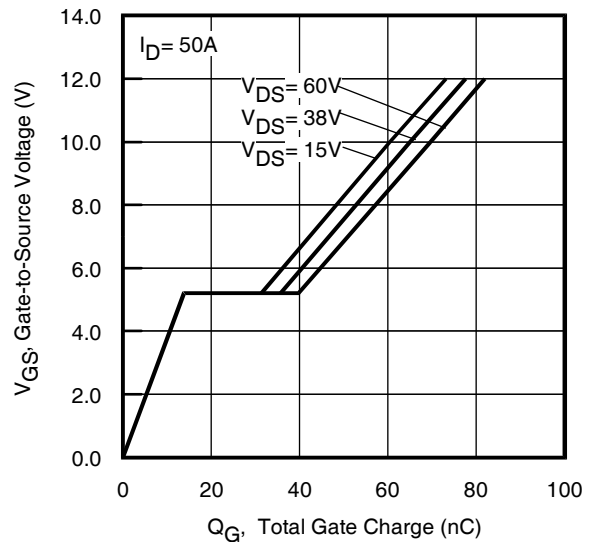
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	250	mJ
I <sub>AR</sub>	Avalanche Current ①	—	50	A

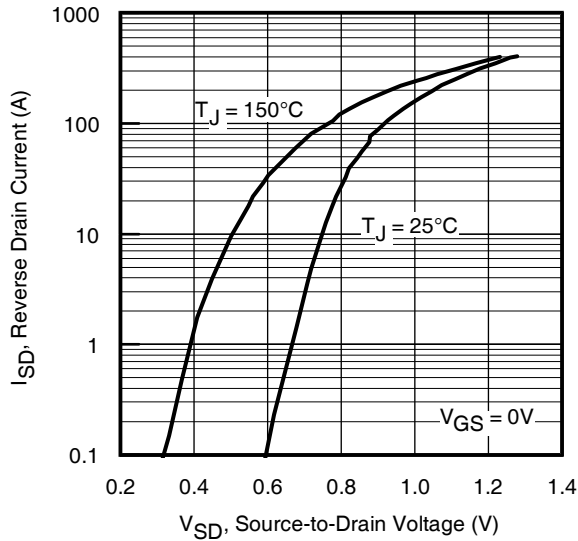
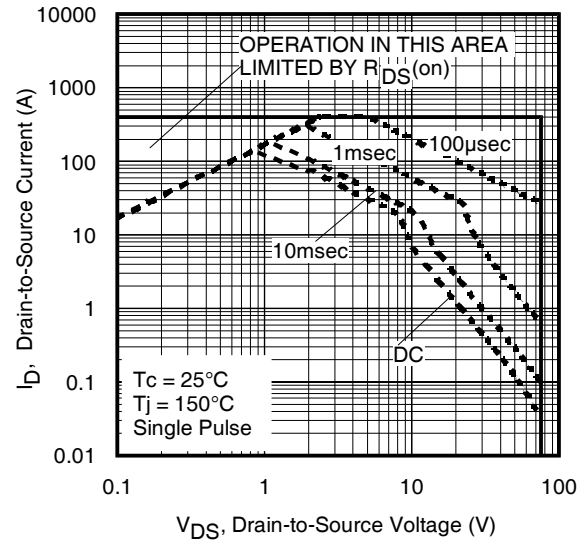
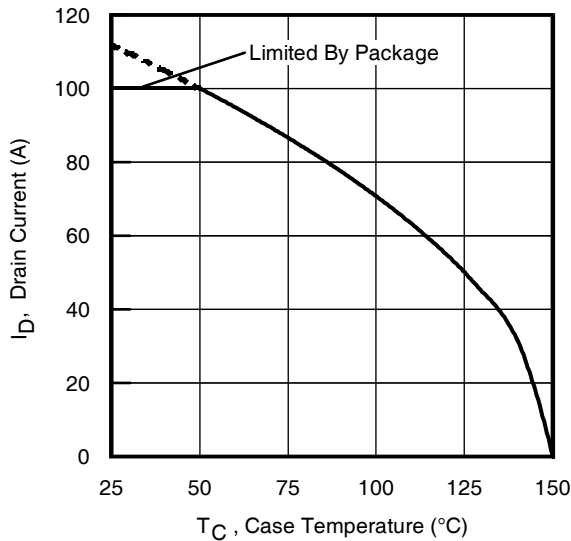
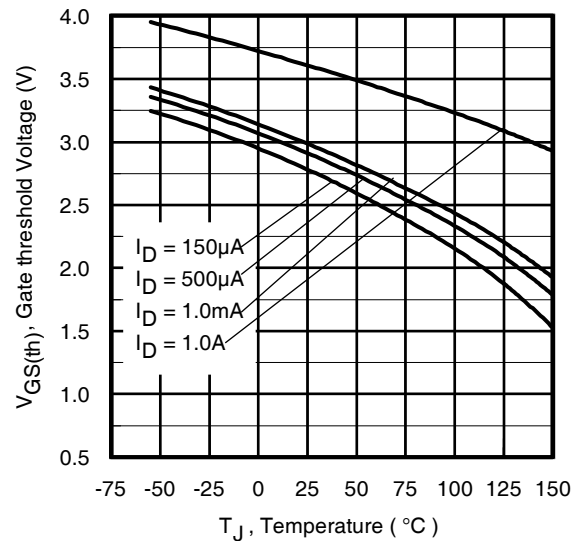
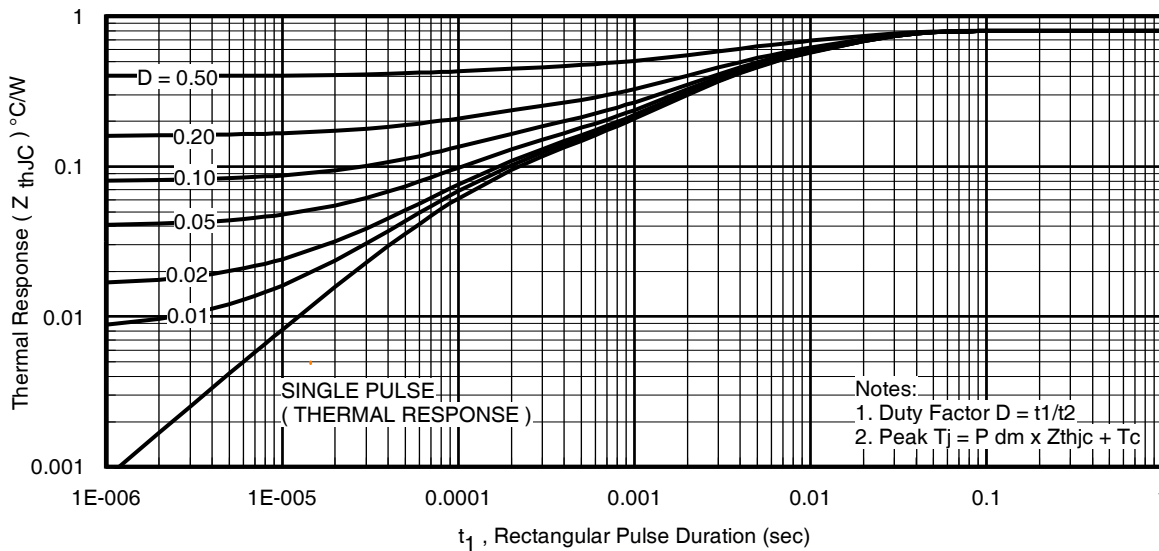
**Diode Characteristics**

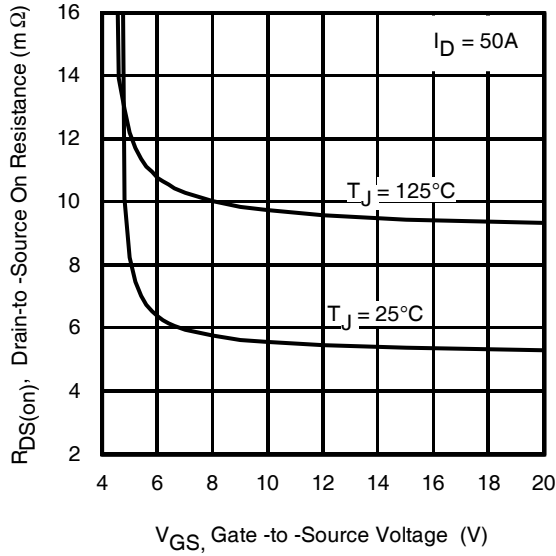
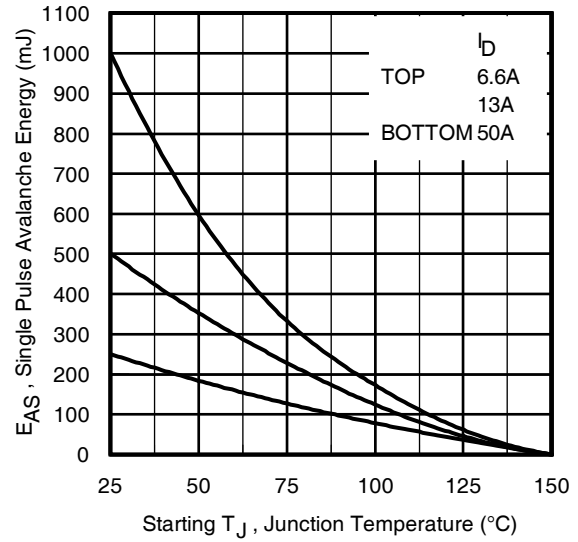
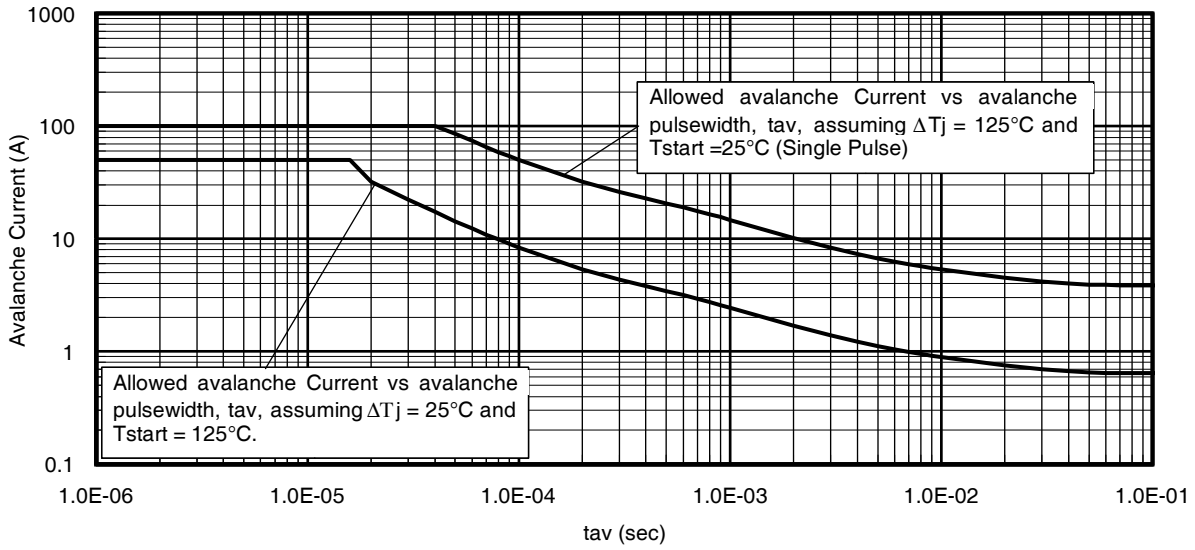
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode) ⑥	—	—	100	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	400		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 50A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	31	47	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 50A, V <sub>DD</sub> = 38V
Q <sub>rr</sub>	Reverse Recovery Charge	—	170	255	nC	di/dt = 500A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Time is dominated by parasitic Inductance				

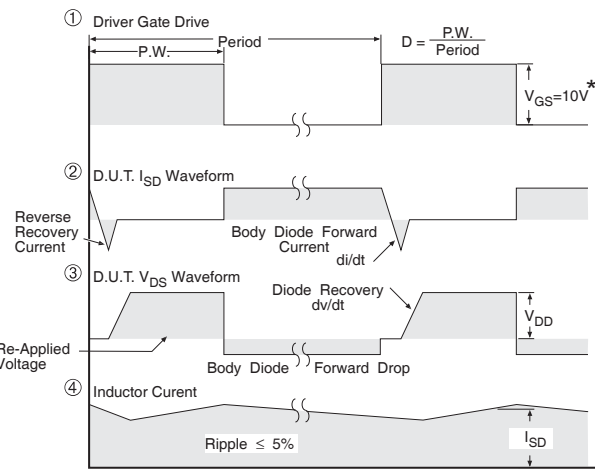
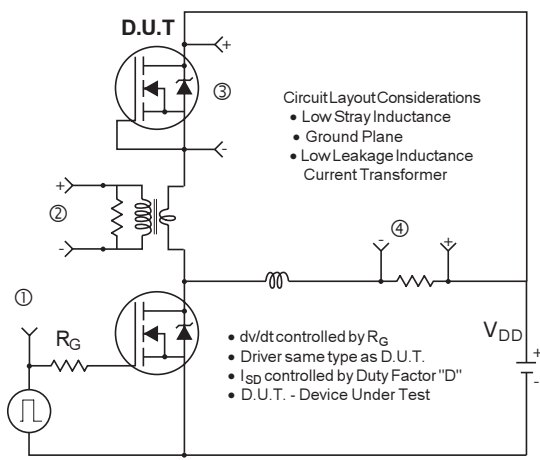
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC-mb</sub>	Junction-to-Mounting Base	0.5	0.8	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	15	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	35	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	22	


**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**

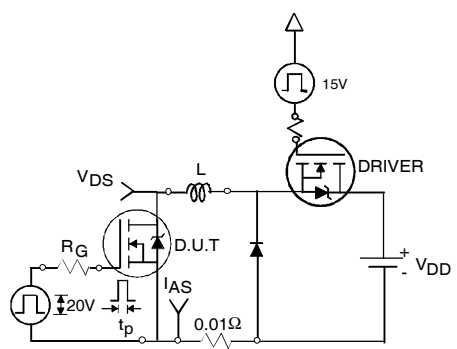

**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Threshold Voltage vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Mounting Base


**Fig 12. On-Resistance vs. Gate Voltage**

**Fig 13. Maximum Avalanche Energy vs. Drain Current**

**Fig 14. Typical Avalanche Current vs. Pulsewidth**

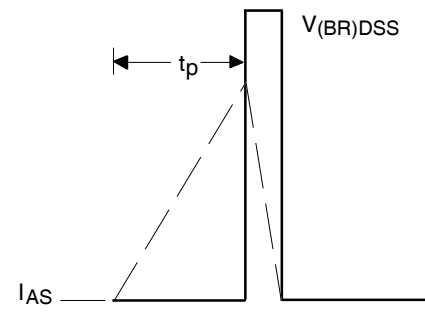


\*  $V_{GS} = 5V$  for Logic Level Devices

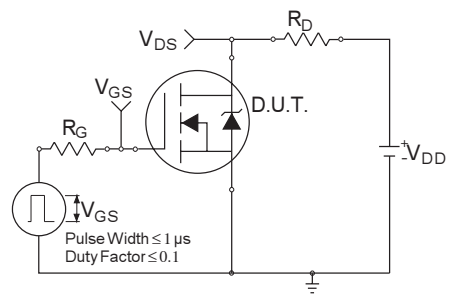
**Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET<sup>®</sup> Power MOSFETs**



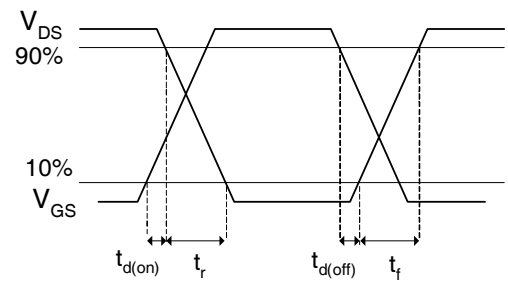
**Fig 16a. Unclamped Inductive Test Circuit**



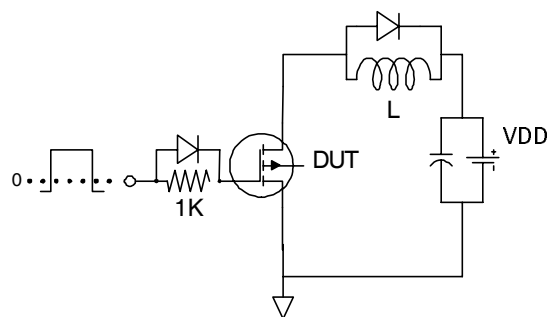
**Fig 16b. Unclamped Inductive Waveforms**



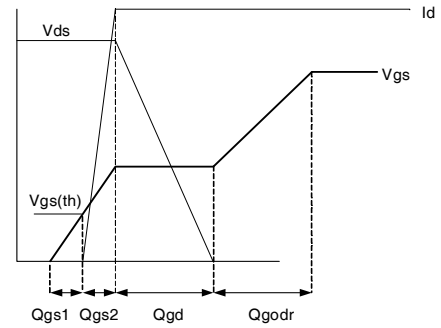
**Fig 17a. Switching Time Test Circuit**



**Fig 17b. Switching Time Waveforms**

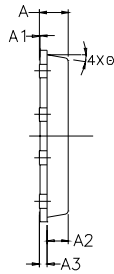


**Fig 18a. Gate Charge Test Circuit**

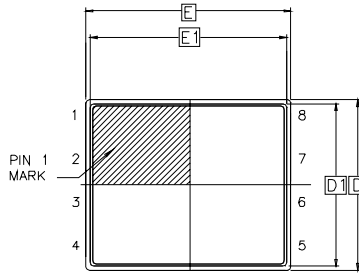


**Fig 18b. Gate Charge Waveform**

## PQFN 5x6 Outline "B" Package Details

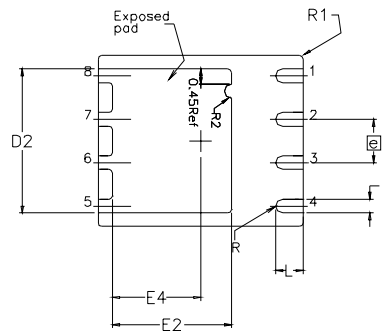


SIDE VIEW



TOP VIEW

DIM SYMBOL	MIN	NOM	MAX
A	0.800	0.830	1.05
A1	0.000	0.020	0.050
A2	0.580	0.630	0.680
A3		0.254 REF	
Ø	0"	10"	12"
b	0.350	0.400	0.470
D	4.850	5.000	5.150
D1	4.675	4.750	5.000
D2	3.700	4.210	4.300
e		1.270 BSC	
E	5.850	6.000	6.150
E1	5.675	5.750	6.000
E2	3.380	3.480	3.760
E4	2.480	2.580	2.680
L	0.550	0.800	0.900
R		0.200 REF	
R1		0.100 REF	
R2	0.150	0.200	0.250



BOTTOM VIEW

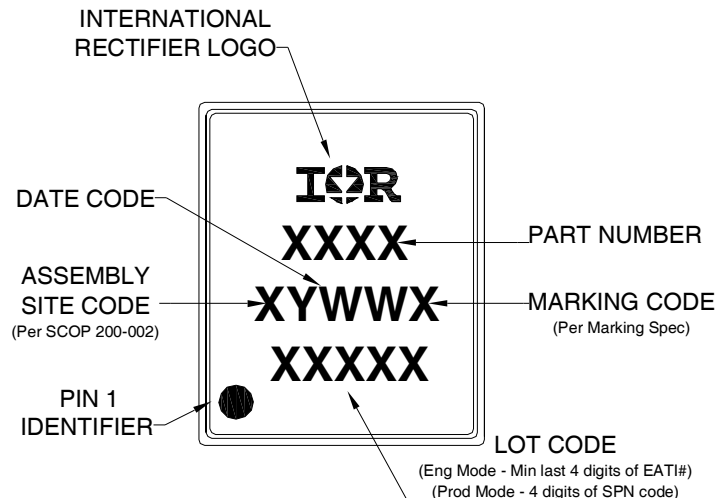
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

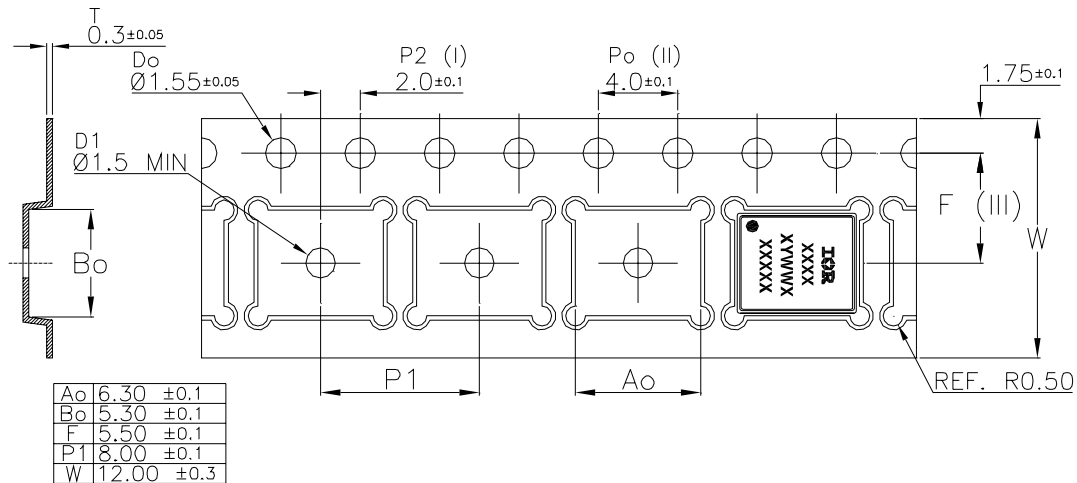
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

## PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

## PQFN 5x6 Outline "B" Tape and Reel



### Qualification information<sup>†</sup>

Qualification level	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site  
<http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.20\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 50\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 100A by production test capability.